

ROITHNER LASERTECHNIK

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RLT65200G TECHNICAL DATA



High Power Visible Laserdiode

Structure **High Efficiency MOVCD Quantum Well Design**

Lasing wavelength **650 nm typ.**

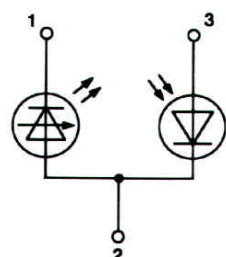
Output power **200 mW, CW**

Package **9 mm G**

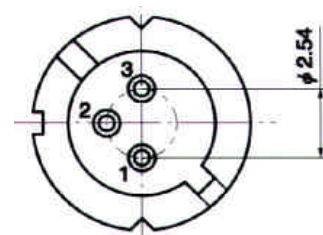


NOTE!
 LASERDIODE
 MUST BE COOLED!

PIN CONNECTION:



- 1) Laser diode cathode
- 2) Laser diode anode and photodiode cathode
- 3) Photodiode anode



Absolute Maximum Ratings (T_c=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Optical Output Power	P _o	220	mW
LD Reverse Voltage	V _{R(LD)}	2	V
PD Reverse Voltage	V _{R(PD)}	30	V
Operating Temperature	T _c	-10 .. +28	°C
Storage Temperature	T _{STG}	-40 .. +80	°C

Optical-Electrical Characteristics (T_c = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Optical Output Power	P _o	Kink free		200	220	mW
Threshold Current	I _{th}			250	300	mA
Operation Current	I _{op}	P _o = 200 mW		500	600	mA
Operation Voltage	V _{op}	P _o = 200 mW	2.1	2.3	2.5	V
Operating Temperature	T _c		20	25	28	°C
Slope Efficiency	η		0.4	0.7	1.0	W/A
Lasing Wavelength	λ	P _o = 200 mW	650	660	665	nm
Beam Divergence	θ	P _o = 200 mW	5	9	14	°
Beam Divergence	θ _⊥	P _o = 200 mW	30	38	45	°
Lasing Aperture	A	P _o = 200 mW		70x1		μm ²
Monitor Current	I _m	P _o = 200 mW		2.0	8.0	mA